RoHS Compliant

Magnachip

MDES10N025RH

Single N-channel Trench MOSFET 100V, 180A, 2.5mΩ

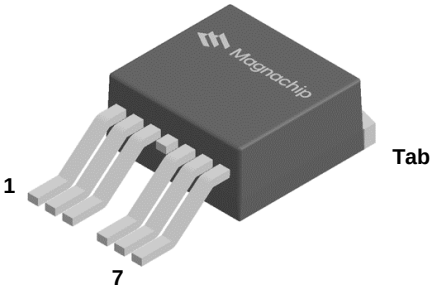
General Description

The MDES10N025RH uses advanced Magnachip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance, and excellent quality.

These devices can also be utilized in industrial applications such as Low Power Drives of E-Vehicles(E-bike), DC/DC converter, and general purpose applications.

Features

- V_{DS} = 100V
- I_D = 180A @V_{GS} = 10V
- Very low on-resistance $R_{DS(ON)}$ < 2.5 mΩ @V_{GS} = 10V
- 100% Avalanche Tested
- 100% Rg Tested
- 100% △V_{DS} Tested



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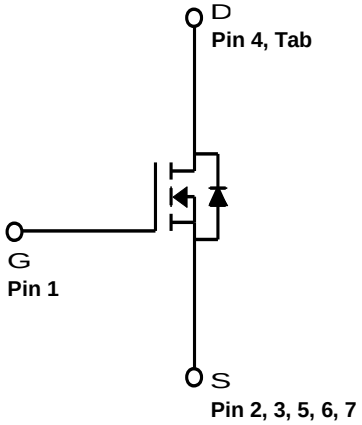

Absolute Maximum Ratings (T_J = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (1)	T_C=25°C (Silicon Limited)	I_D	280	A
	T_C=25°C (Package Limited)		180	
	T_C=100°C (Silicon Limited)		198	
Pulsed Drain Current (2)		I_{DM}	720	
Power Dissipation	T_C=25°C	P_D	416	W
	T_C=100°C		208	
Single Pulse Avalanche Energy (3)		E_{AS}	544	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~175	°C

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.36	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDES10N025RH	-55~175ºC	TO-263-7L	Tape & Reel	Halogen Free

Electrical Characteristics (T_J =25ºC)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0	-	4.0	
Drain Cut-Off Current	I_{DSS}	V_{DS} = 100V, V_{GS} = 0V	-	-	1.0	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±0.1	
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 100A	-	2.2	2.5	mΩ
Forward Transconductance	g_{fs}	V_{DS} = 10V, I_D = 100A	-	130	-	S
Dynamic Characteristics						
Total Gate Charge	Q_g	V_{DS} = 50V, I_D = 50A, V_{GS} = 10V	-	147	-	nC
Gate-Source Charge	Q_{gs}		-	42	-	
Gate-Drain Charge	Q_{gd}		-	28	-	
Input Capacitance	C_{iss}	V_{DS} = 40V, V_{GS} = 0V, f = 1.0MHz	-	10,420	-	pF
Reverse Transfer Capacitance	C_{rss}		-	75	-	
Output Capacitance	C_{oss}		-	2,050	-	
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 10V, V_{DS} = 50V, I_D = 100A , R_G = 3.0Ω	-	32	-	ns
Rise Time	t_r		-	27	-	
Turn-Off Delay Time	$t_{d(off)}$		-	98	-	
Fall Time	t_f		-	26	-	
Gate Resistance	Rg	f=1 MHz	-	3.0	-	Ω
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	I_S = 100A, V_{GS} = 0V	-	0.9	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 100A, dI/dt = 100A/μs	-	127		ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	416		nC

Note :

1. Surface mounted FR-4 board by JEDEC (jesd51-7). Continuous current at T_C=25℃ is silicon limited
2. Pulse width limited by T_{Jmax}
3. E_{AS} is tested at starting Tj = 25℃, L = 1.0mH, I_{AS} = 33A, V_{GS} = 10V.

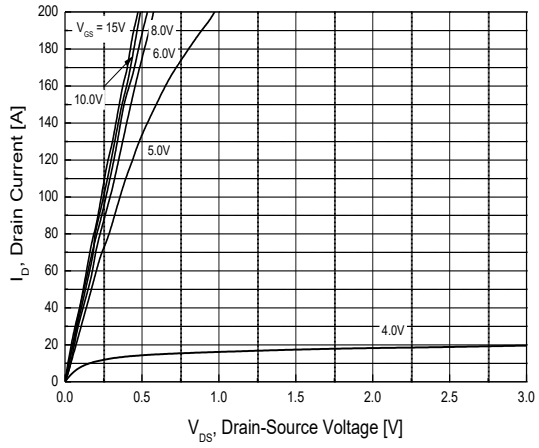

Fig.1 On-Region Characteristics

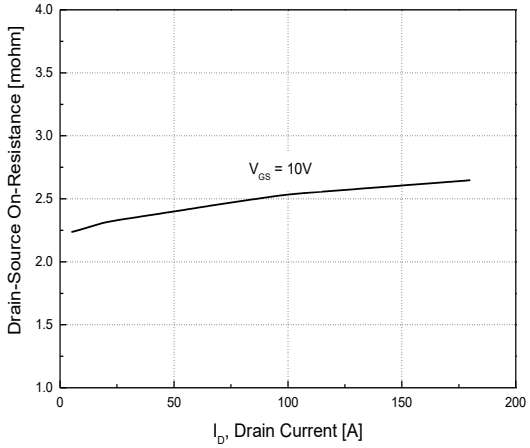

Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

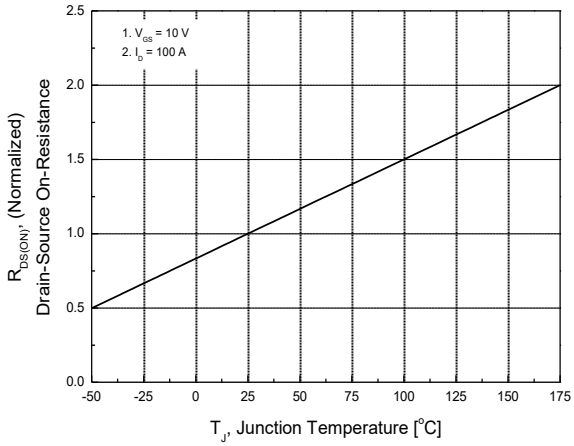

Fig.3 On-Resistance Variation with Temperature

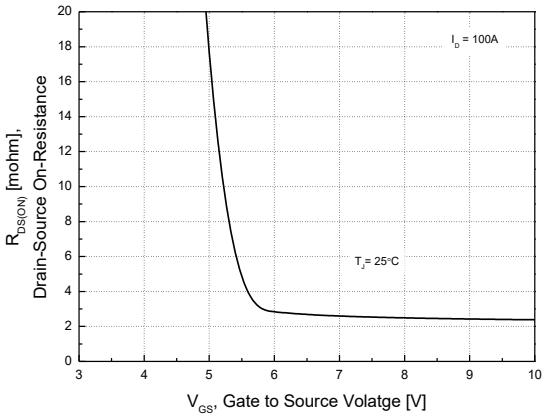

Fig.4 On-Resistance Variation with Gate to Source Voltage

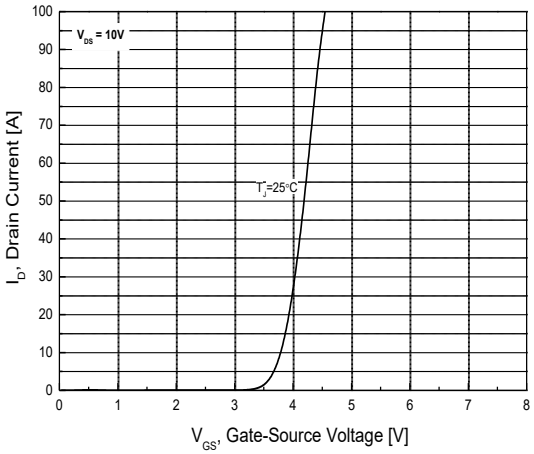

Fig.5 Transfer Characteristics

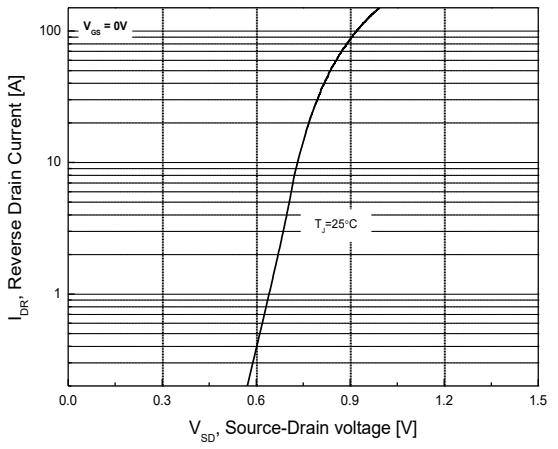

Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

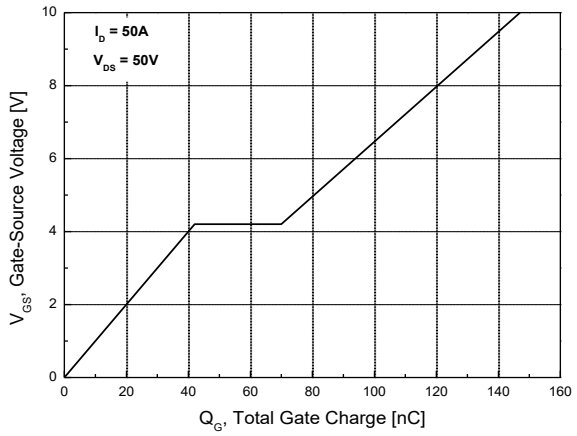

Fig.7 Gate Charge Characteristics

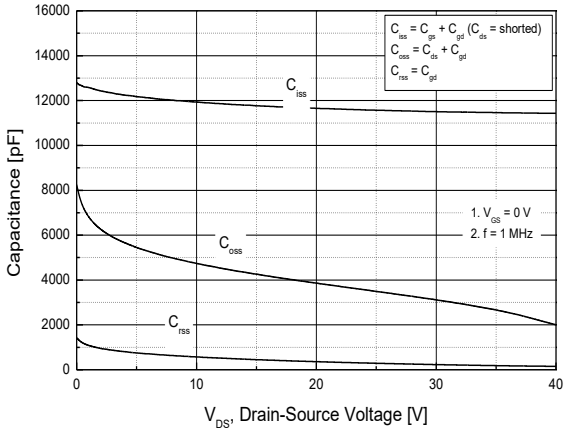

Fig.8 Capacitance Characteristics

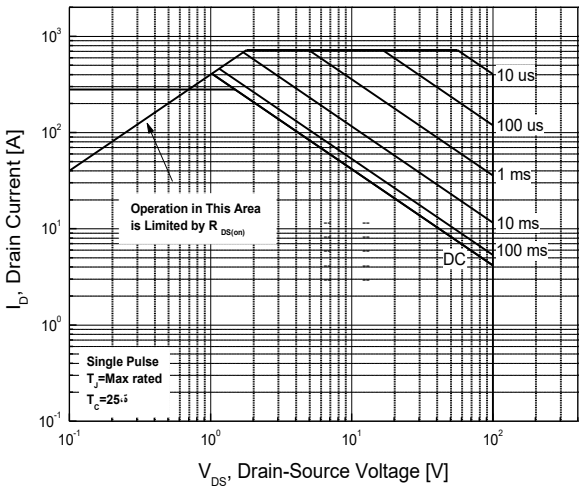

Fig.9 Maximum Safe Operating Area

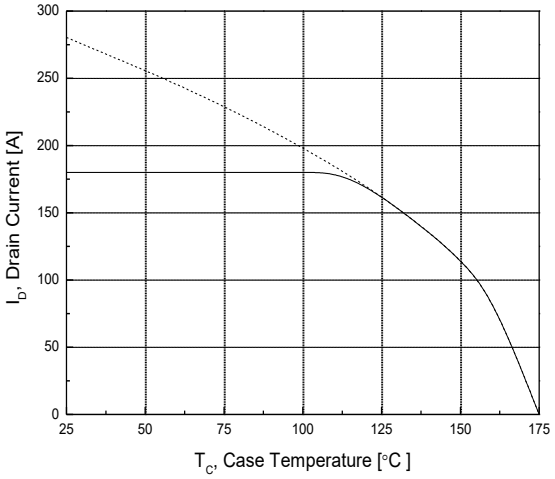

Fig.10 Maximum Drain Current vs. Case Temperature

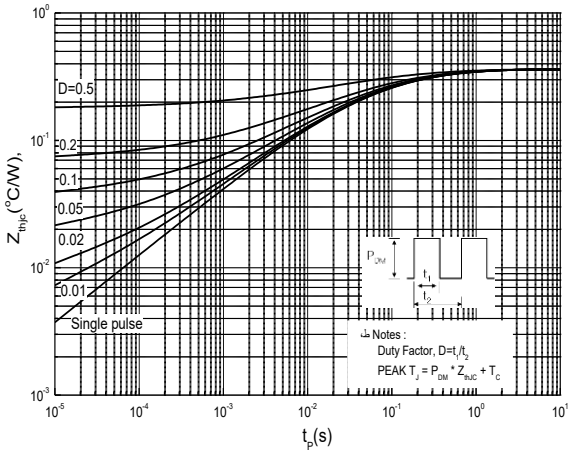

Fig.11 Transient Thermal Response Curve

Package Dimension

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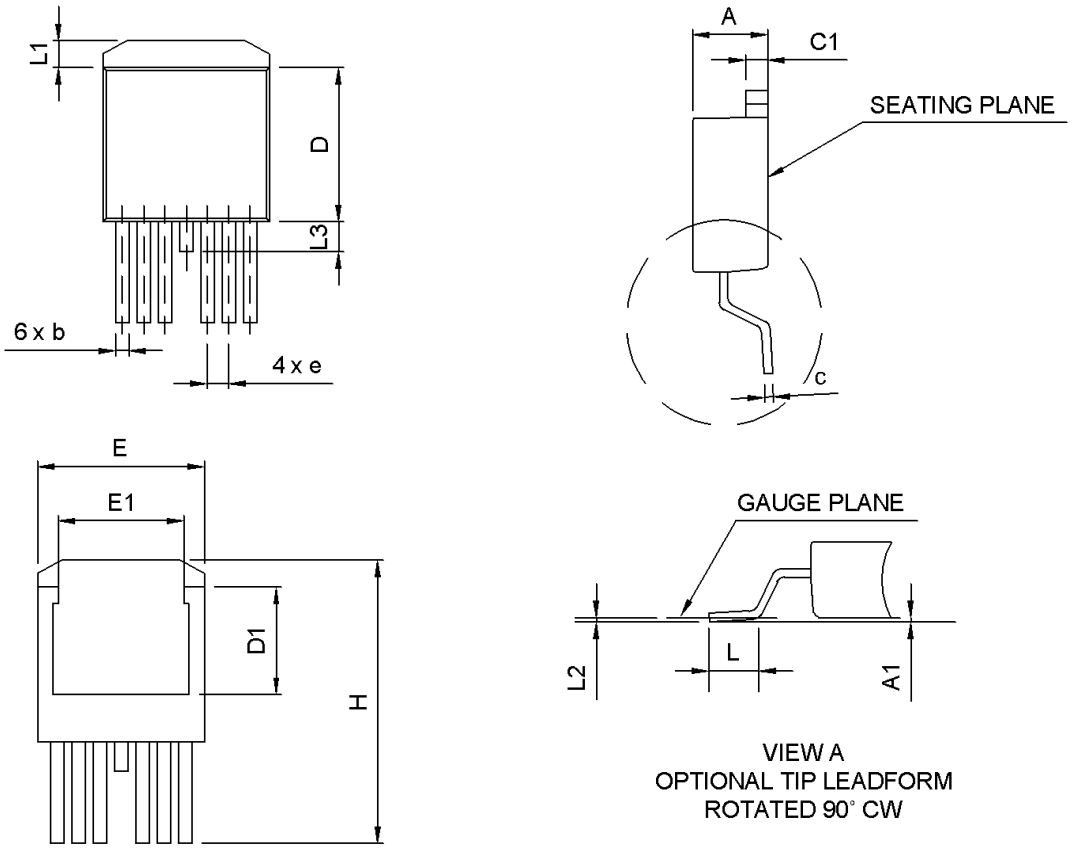
Dimensions are in millimeters unless otherwise specified



Symbol	Dimension [mm]	
	Min	Max
A	4.30	4.70
A1	-	0.254
b	0.65	0.90
c	0.40	0.60
c1	1.25	1.40
D	9.00	9.40
D1	5.90	6.90
E	9.68	10.20
E1	7.70	8.50
e	1.27BSC	
H	14.61	15.88
L	1.78	2.80
L1	-	1.6
L2	0.254BSC	
L3	-	1.78

Note : Package body size, length and width do not include mold flash, protrusions and gate burrs.

DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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